

AMENDMENTS TO THE CLAIMS

Claims 1-51 (Canceled)

Claim 52 (Currently Amended): A method of treating a dielectric film comprising:

etching a portion of said dielectric film so as to form in said dielectric film a sidewall surface; and

exposing ~~at least one said sidewall surface of said dielectric film~~ to at least one of TMCTS and OMCTS, wherein

said dielectric film has a dielectric constant value less than the dielectric constant of SiO<sub>2</sub>.

Claim 53 (Canceled)

Claim 54 (New): The method according to Claim 52, further comprising

forming a mask on said dielectric film; and

forming a pattern in said mask, wherein

said etching comprises transferring said pattern in said mask to said dielectric film.

Claim 55 (New): The method according to Claim 52, further comprising exposing said sidewall surface to at least one of a nitrogen containing material and a chlorine containing material.

Claim 56 (New): The method according to Claim 52, wherein said dielectric film has a dielectric constant in a range of from 1.6 to 2.7.

Claim 57 (New): The method according to Claim 52, wherein said dielectric film is porous.

Claim 58 (New): The method according to Claim 52, wherein said dielectric film is non-porous.

Claim 59 (New): The method according to Claim 52, further comprising heating said dielectric film to a temperature in a range of from 50C to 400C.

Claim 60 (New): The method according to Claim 52, wherein said sidewall surface is exposed to TMCTS.

Claim 61 (New): The method according to Claim 52, wherein said sidewall surface is exposed to OMCTS.